#### P-CHANNEL ENHANCEMENT MODE MOSFET

#### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
	39mΩ @ V <sub>GS</sub> = -4.5V	-2.5A
-16V	52mΩ @ V <sub>GS</sub> = -2.5V	-2.1A
	65mΩ @ V <sub>GS</sub> = -1.8V	-1.8A

#### **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

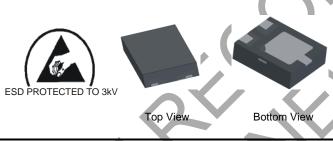
- Backlighting
- **Power Management Functions**
- DC-DC Converters

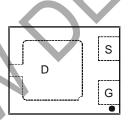
#### **Features and Benefits**

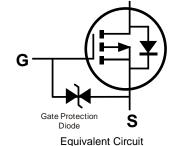
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 3kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMG3415UFY4Q)

#### **Mechanical Data**

- Case: X2-DFN2015-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208@4
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)







Internal Schematic (Top View)

Ordering Information (Note 4)

	Part Number	Case	Packaging
	DMG3415UFY4-7	X2-DFN2015-3	3,000/Tape & Reel
Notes:	1. No purposely added lead, Fully EU Direct	tive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/8	363/EU (RoHS 3) compliant.

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- See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**

34P **YM** 

34P = Marking Code YM = Date Code Marking Y = Year (ex: F = 2018)M = Month (ex: 9 = September)

#### Date Code Key

Year	2009	-	-	2015	2016	20	17	2018	2019	20	20	2021
Code	W	-	-	С	D		E	F	G	I	Н	
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# NOT RECOMMENDED FOR NEW DESIGN USE DMP2045UFY4

**DMG3415UFY4** 

## **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		$V_{DSS}$	-16	V
Gate-Source Voltage		V <sub>GSS</sub>	±8	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = -4.5V	Steady State	I <sub>D</sub>	-2.5 -2.2	Α
Pulsed Drain Current (Note 6)		I <sub>DM</sub>	-12	Α

## **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		$P_{D}$	0.65	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	197	°C/W
Total Power Dissipation (Note 6)		$P_{D}$	1.35	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ hetaJA}$	95	°C/W
Thermal Resistance, Junction to Case (Note 6)		$R_{ heta JC}$	22	
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C

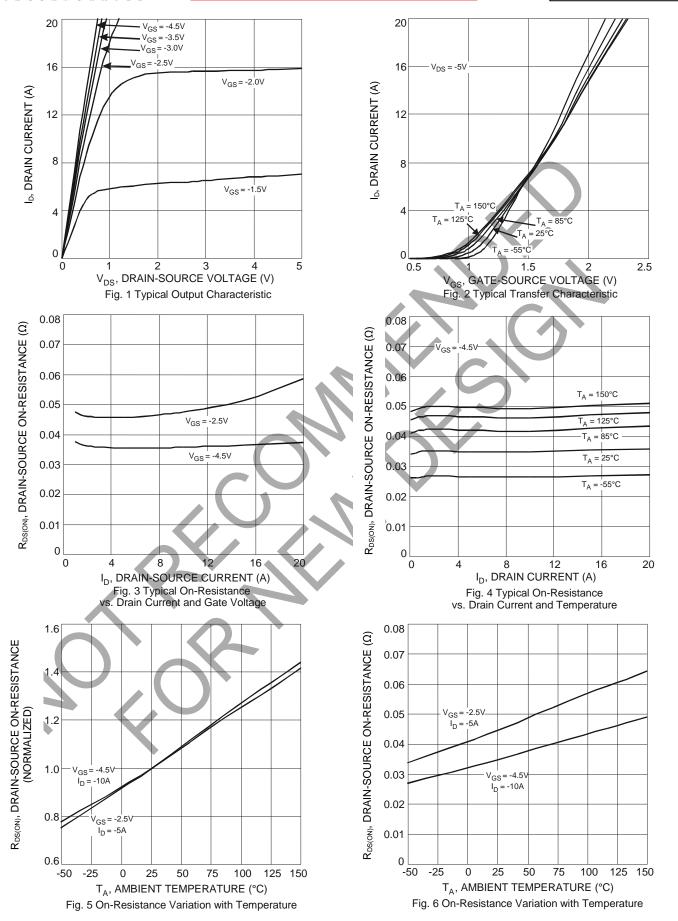
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-16	1		V	$V_{GS} = 0V, I_{D} = -250\mu A$
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	<b>—</b>		-1.0	μA	$V_{DS} = -16V, V_{GS} = 0V$
Gate-Source Leakage	Logo			±10	μΑ	$V_{GS} = \pm 8V$ , $V_{DS} = 0V$
Gate-Source Leakage	IGSS			±500	nA	$V_{GS} = \pm 5V$ , $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.3	-0.55	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
		7	31	39		$V_{GS} = -4.5V, I_D = -4.0A$
Static Drain-Source On-Resistance	RDS(ON)		40	52	mΩ	$V_{GS} = -2.5V, I_D = -3.5A$
			51	65		$V_{GS} = -1.8V, I_D = -2.0A$
Forward Transfer Admittance	Y <sub>fs</sub>	_	7.9	_	S	$V_{DS} = -5V, I_{D} = -2.5A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C <sub>iss</sub>		282	_	pF	V 40V V 0V
Output Capacitance	Coss	_	152	_	pF	$V_{DS} = -10V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	38	_	pF	1 = 1.0IVII IZ
Gate Resistance	$R_{g}$		250	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge	Qg		10	_	nC	
Gate-Source Charge	$Q_{gs}$		1.5	_	nC	$V_{GS} = -4.5V$ , $V_{DS} = -10V$ , $I_{D} = -4A$
Gate-Drain Charge	$Q_{gd}$		2.4	_	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	_	79	_	ns	
Turn-On Rise Time		1	175		ns	$V_{DS} = -10V, V_{GS} = -4.5V,$
Turn-Off Delay Time	t <sub>D(OFF)</sub>		885		ns	$R_D = 2.5\Omega$ , $R_G = 3.0\Omega$
Turn-Off Fall Time	t <sub>F</sub>	_	568	_	ns	

Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.







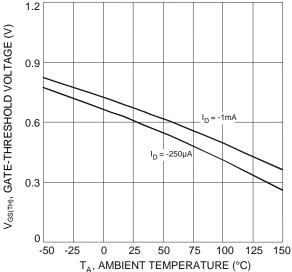
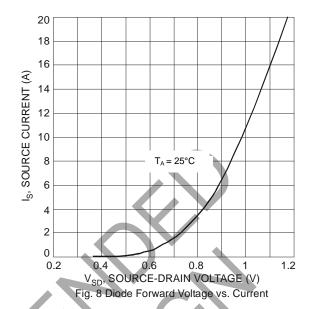
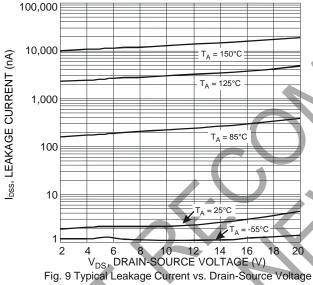


Fig. 7 Gate Threshold Variation vs. Ambient Temperature





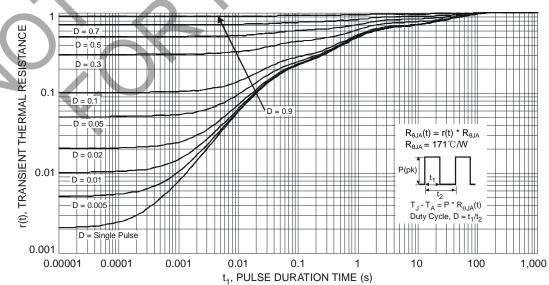


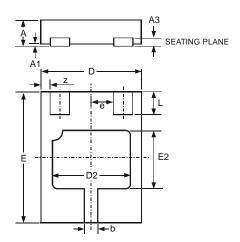
Fig. 10 Transient Thermal Response



### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### X2-DFN2015-3

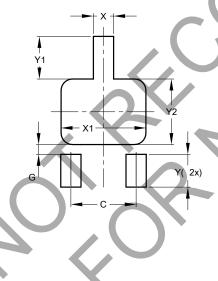


X2-DFN2015-3							
Dim	Min	Max	Тур				
Α	ı	0.40	-				
A1	0	0.05	0.02				
A3	-	-	0.13				
b	0.20	0.30	0.25				
D	1.45	1.575	1.5				
D2	1.00	1.20	1.10				
е	-	-	0.50				
Е	1.95	2.075	2.00				
E2	0.70	0.90	0.80				
L	0.25	0.35	0.30				
Z	-	6	0.125				
All Dimensions in mm							

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### X2-DFN2015-3



X2-DFN2015-3					
Dimensions	Value (in mm)				
С	1.000				
G	0.150				
Х	0.310				
X1	1.300				
Υ	0.500				
Y1	0.650				
Y2	1.000				



## NOT RECOMMENDED FOR NEW DESIGN USE DMP2045UFY4

**DMG3415UFY4** 

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